

μClamp0561P-μClamp6061P

High Power MicroClamp® 1-Line ESD and Surge Protection

PROTECTION PRODUCTS

Description

μClamp® TVS diodes are designed to protect sensitive electronics from damage or latch-up due to EOS, lightning, CDE, and ESD. They feature large cross-sectional area junctions for conducting high transient currents. These devices offer desirable characteristics for board level protection including fast response time, low operating and clamping voltage, and no device degradation.

μClamp®xx61P series are designed for for use in harsh transient environments. They feature extremely good protection characteristics highlighted by high surge current capability, low peak ESD clamping voltage, and high ESD withstand voltage. Device options are available for protecting data or power lines operating at 5V to 60V.

μClamp®xx61P are in a 2-pin SLP1608P2 package measuring 1.6 x 0.8 mm with a nominal height of 0.50mm. The leads are finished with lead-free NiPdAu. High surge current capability and low clamping voltage making them ideal for protecting VBus, battery, and other power lines in consumer and industrial electronics.

Features

- · Transient Protection to
 - IEC 61000-4-2 (ESD) 30kV (Air), 30kV (Contact)
 - IEC 61000-4-4 (EFT) 4kV (5/50ns)
 - IEC 61000-4-5 (Lightning) 8-80A (8/20µs)
- · Protects one data or power line
- Working voltage options: 5V, 10V, 12V, 15V, 24V, 30V, 36V, 40V, 60V
- Low leakage current
- · High peak pulse current capability
- Solid-state silicon-avalanche technology

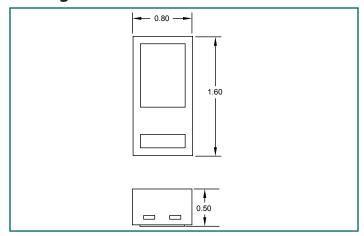
Mechanical Characteristics

- SLP1608P2 package
- Pb-Free, Halogen Free, RoHS/WEEE compliant
- Nominal Dimensions: 1.6 x 0.8 x 0.50 mm
- · Lead Finish: NiPdAu
- Marking: Marking code
- Packaging: Tape and Reel

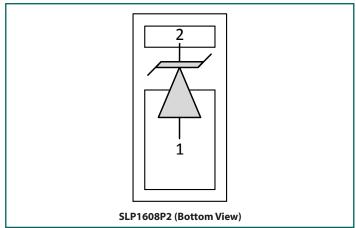
Applications

- Cellular Handsets
- Industrial Equipment
- Microcontroller RESET and IRQ Pins
- USB Voltage Bus
- Battery protection
- Tablet PC
- CCTV Cameras
- Instrumentation

Package Dimension



Schematic & Pin Configuration



Absolute Maximum Ratings

Rating	Symbol	Value	Units
Peak Pulse Power (tp = $8/20\mu s$)	P _{PK}	1200-1600	W
Peak Pulse Current (tp = 8/20μs)	I _{PP}	8-80	Α
ESD per IEC 61000-4-2 (Contact) ⁽¹⁾ ESD per IEC 61000-4-2 (Air) ⁽¹⁾	V _{ESD}	±30 ±30	kV
Operating Temperature	T,	-40 to +125	°C
Storage Temperature	T _{STG}	-55 to +150	°C

Electrical Characteristics (T=25°C unless otherwise specified)

μClamp0561P								
Parameter	Symbol	Conditions	Conditions		Тур.	Max.	Units	
Reverse Stand-Off Voltage	V _{RWM}	-40°C to 125°C, Pin 2	2 to Pin 1			5	V	
Reverse Breakdown Voltage	V _{BR}	I _t = 1mA, Pin 2 to Pi	n 1	6	7	9	V	
Reverse Leakage Current	I _R	$V_{RWM} = 5V$	T = 25°C		50	300	nA	
Peak Pulse Current	I _{PP}	tp = 8/20μs				80	Α	
Clamping Voltage ⁽²⁾	V _C	$I_{pp} = 40A$, tp = 8/20 μ	ıs, Pin 2 to Pin 1			12	V	
Clamping Voltage ⁽²⁾	V _C	$I_{pp} = 80A$, tp = 8/20 μ	ıs, Pin 2 to Pin 1			15	V	
Dynamic Resistance(3), (4)	R _{DYN}	tp = 0.2/100ns (TLP), Pin 2 to Pin 1			0.05		Ohms	
Junction Capacitance	C _J	$V_R = 0V, f = 1MHz$ Pin 2 to Pin 1	T = 25°C			800	pF	

Notes:

^{(1):} ESD Gun return path to Ground Reference Plane (GRP)

^{(2):}Tested using a constant current source

^{(3):} Transmission Line Pulse Test (TLP) Settings: tp = 100ns, tr = 0.2ns, I_{TLP} and V_{TLP} averaging window: $t_1 = 70$ ns to $t_2 = 90$ ns.

^{(4):} Dynamic resistance calculated from $I_{TLP} = 4A$ to $I_{TLP} = 16A$

μClamp1061P							
Parameter	Symbol	Conditions	Conditions		Тур.	Max.	Units
Reverse Stand-Off Voltage	V _{RWM}	-40°C to 125°C, Pin	2 to Pin 1			10	V
Reverse Breakdown Voltage	V _{BR}	$I_t = 1 \text{mA}$, Pin 2 to Pi	I ₊ = 1mA, Pin 2 to Pin 1		13.5	15.5	V
Reverse Leakage Current	l _R	$V_{RWM} = 10V$	T = 25°C		<10	100	nA
Peak Pulse Current	l _{PP}	tp = 8/20μs				60	Α
Clamping Voltage ⁽²⁾	V _C	$I_{pp} = 10A$, $tp = 8/20\mu$	ıs, Pin 2 to Pin 1			17	V
Clamping Voltage ⁽²⁾	V _C	$I_{pp} = 60A$, $tp = 8/20\mu$	ıs, Pin 2 to Pin 1			25	٧
Dynamic Resistance(3), (4)	R _{DYN}	tp = 0.2/100ns (TLP), Pin 2 to Pin 1			0.05		Ohms
Junction Capacitance	C _J	$V_R = 0V, f = 1MHz$ Pin 2 to Pin 1	T = 25°C			350	pF

μClamp1261P								
Parameter	Symbol	Conditions	Conditions		Тур.	Max.	Units	
Reverse Stand-Off Voltage	V _{RWM}	-40°C to 125°C, Pin	2 to Pin 1			12	V	
Reverse Breakdown Voltage	V _{BR}	$I_t = 1 \text{mA}$, Pin 2 to Pi	n 1	14	16.5	19	V	
Reverse Leakage Current	I _R	V _{RWM} = 12V	T = 25°C		<10	100	nA	
Peak Pulse Current	I _{PP}	tp = 8/20μs				45	А	
Clamping Voltage ⁽²⁾	V _c	$I_{pp} = 10A$, $tp = 8/20\mu$	ıs, Pin 2 to Pin 1			25	V	
Clamping Voltage ⁽²⁾	V _c	$I_{pp} = 45A$, tp = 8/20 μ	ıs, Pin 2 to Pin 1			33	V	
Dynamic Resistance(3), (4)	R _{DYN}	tp = 0.2/100ns (TLP), Pin 2 to Pin 1			0.05		Ohms	
Junction Capacitance	C _J	$V_R = 0V, f = 1MHz$ Pin 2 to Pin 1	T = 25°C			275	pF	

μClamp1561P								
Parameter	Symbol	Conditions	Conditions		Тур.	Max.	Units	
Reverse Stand-Off Voltage	V _{RWM}	-40°C to 125°C, Pin	2 to Pin 1			15	V	
Reverse Breakdown Voltage	V _{BR}	I _t = 1mA, Pin 2 to Pi	I _t = 1mA, Pin 2 to Pin 1		20	23	V	
Reverse Leakage Current	I _R	$V_{RWM} = 15V$	T = 25°C		<10	100	nA	
Peak Pulse Current	l _{PP}	tp = 8/20μs				40	А	
Clamping Voltage ⁽²⁾	V _C	$I_{pp} = 10A$, tp = 8/20 μ	ıs, Pin 2 to Pin 1			28	V	
Clamping Voltage ⁽²⁾	V _C	$I_{pp} = 40A$, tp = 8/20 μ	ıs, Pin 2 to Pin 1			40	V	
Dynamic Resistance(3), (4)	R _{DYN}	tp = 0.2/100ns (TLP), Pin 2 to Pin 1			0.05		Ohms	
Junction Capacitance	C _J	$V_R = 0V, f = 1MHz$ Pin 2 to Pin 1	T = 25°C			220	pF	

μClamp2461P							
Parameter	Symbol	Conditions	Conditions		Тур.	Max.	Units
Reverse Stand-Off Voltage	V _{RWM}	-40°C to 125°C, Pin	2 to Pin 1			24	V
Reverse Breakdown Voltage	V _{BR}	I _t = 1mA, Pin 2 to Pi	n 1	27	32	36	V
Reverse Leakage Current	I _R	$V_{RWM} = 24V$	T = 25°C		<10	100	nA
Peak Pulse Current	I _{PP}	tp = 8/20μs				23	А
Clamping Voltage ⁽²⁾	V _c	$I_{pp} = 10A$, $tp = 8/20\mu$	us, Pin 2 to Pin 1			50	V
Clamping Voltage ⁽²⁾	V _c	$I_{pp} = 23A$, tp = 8/20 μ	us, Pin 2 to Pin 1			65	V
Dynamic Resistance(3), (4)	R _{DYN}	tp = 0.2/100ns (TLP), Pin 2 to Pin 1			0.20		Ohms
Junction Capacitance	C _J	$V_R = 0V, f = 1MHz$ Pin 2 to Pin 1	T = 25°C			165	рF

μClamp3061P							
Parameter	Symbol	Conditions	Conditions		Тур.	Max.	Units
Reverse Stand-Off Voltage	V _{RWM}	-40°C to 125°C, Pin	2 to Pin 1			30	V
Reverse Breakdown Voltage	V _{BR}	$I_t = 1 \text{mA}$, Pin 2 to Pi	n 1	34	40	42	V
Reverse Leakage Current	I _R	V _{RWM} = 30V	T = 25°C		<10	100	nA
Peak Pulse Current	I _{PP}	tp = 8/20μs				18	Α
Clamping Voltage ⁽²⁾	V _C	$I_{pp} = 10A$, $tp = 8/20\mu$	ıs, Pin 2 to Pin 1			55	V
Clamping Voltage ⁽²⁾	V _C	$I_{pp} = 18A, tp = 8/20\mu$	ıs, Pin 2 to Pin 1			65	V
Dynamic Resistance(3), (4)	R _{DYN}	tp = 0.2/100ns (TLP), Pin 2 to Pin 1			0.25		Ohms
Junction Capacitance	C _J	$V_R = 0V, f = 1MHz$ Pin 2 to Pin 1	T = 25°C			155	pF

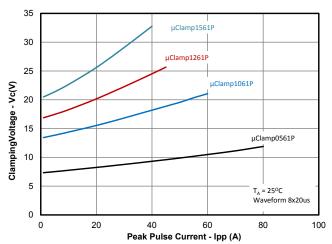
μClamp3661P							
Parameter	Symbol	Conditions	Conditions		Тур.	Max.	Units
Reverse Stand-Off Voltage	V _{RWM}	-40°C to 125°C, Pin	2 to Pin 1			36	V
Reverse Breakdown Voltage	V _{BR}	$I_t = 1$ mA, Pin 2 to Pir	า 1	37	40	44	V
Reverse Leakage Current	I _R	$V_{RWM} = 36V$	T = 25°C		<10	100	nA
Peak Pulse Current	I _{PP}	tp = 8/20μs				18	А
Clamping Voltage ⁽²⁾	V _c	$I_{pp} = 2A$, $tp = 8/20 \mu s$, Pin 2 to Pin 1			48	V
Clamping Voltage ⁽²⁾	V _c	$I_{pp} = 18A, tp = 8/20\mu$	ıs, Pin 2 to Pin 1			70	V
Dynamic Resistance(3), (4)	R _{DYN}	tp = 0.2/100ns (TLP), Pin 2 to Pin 1			0.25		Ohms
Junction Capacitance	C _J	$V_R = 0V, f = 1MHz$ Pin 2 to Pin 1	T = 25°C			150	pF

μClamp4061P								
Parameter	Symbol	Conditions	Conditions		Тур.	Max.	Units	
Reverse Stand-Off Voltage	V _{RWM}	-40°C to 125°C, Pin	2 to Pin 1			40	V	
Reverse Breakdown Voltage	V _{BR}	$I_t = 1$ mA, Pin 2 to Pir	I _t = 1mA, Pin 2 to Pin 1		50	55	V	
Reverse Leakage Current	l _R	V _{RWM} = 40V	T = 25°C		<10	100	nA	
Peak Pulse Current	l _{pp}	tp = 8/20μs				12	А	
Clamping Voltage ⁽²⁾	V _c	$I_{pp} = 12A$, $tp = 8/20\mu$	ıs, Pin 2 to Pin 1			80	V	
Dynamic Resistance ^{(3), (4)}	R _{DYN}	tp = 0.2/100ns (TLP), Pin 2 to Pin 1			0.35		Ohms	
Junction Capacitance	C _J	$V_R = 0V, f = 1MHz$ Pin 2 to Pin 1	T = 25°C			125	pF	

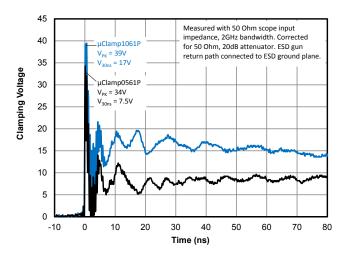
μClamp6061P								
Parameter	Symbol	Conditions	Conditions		Тур.	Max.	Units	
Reverse Stand-Off Voltage	V _{RWM}	-40°C to 125°C, Pin	2 to Pin 1			60	V	
Reverse Breakdown Voltage	V _{BR}	$I_t = 1 \text{mA}$, Pin 2 to Pir	I _t = 1mA, Pin 2 to Pin 1		70	85	V	
Reverse Leakage Current	I _R	V _{RWM} = 60V	T = 25°C		<10	100	nA	
Peak Pulse Current	l _{pp}	tp = 8/20µs				8	А	
Clamping Voltage ⁽²⁾	V _c	$I_{pp} = 8A$, tp = 8/20µs	, Pin 2 to Pin 1			105	V	
Dynamic Resistance ^{(3), (4)}	R _{DYN}	tp = 0.2/100ns (TLP) Pin 2 to Pin 1			0.45		Ohms	
Junction Capacitance	C _J	$V_R = 0V, f = 1MHz$ Pin 2 to Pin 1	T = 25°C			110	pF	

Typical Characteristics

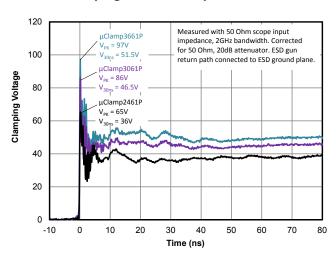
Clamping Voltage vs. Peak Pulse Current ($V_{RWM} = 5V - 15V$)



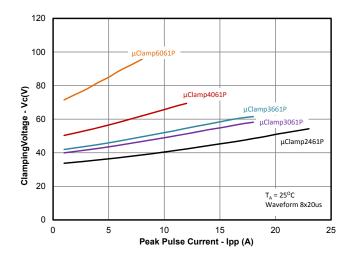
ESD Clamping (8kV Contact per IEC 61000-4-2)



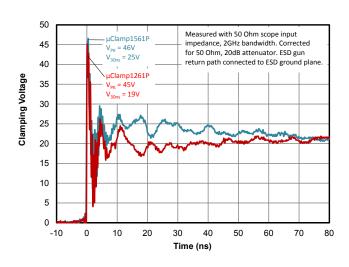
ESD Clamping (8kV Contact per IEC 61000-4-2)



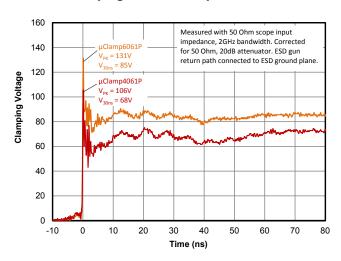
Clamping Voltage vs. Peak Pulse Current (V_{RWM} = 24V - 60V)



ESD Clamping (8kV Contact per IEC 61000-4-2)

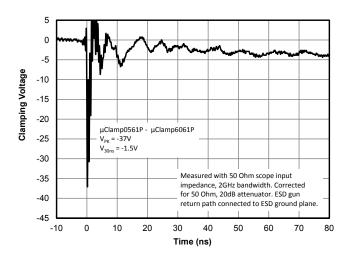


ESD Clamping (8kV Contact per IEC 61000-4-2)

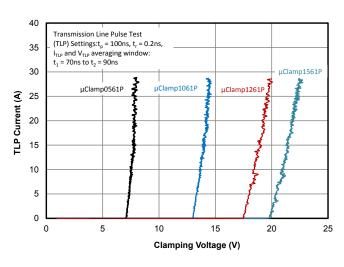


Typical Characteristics

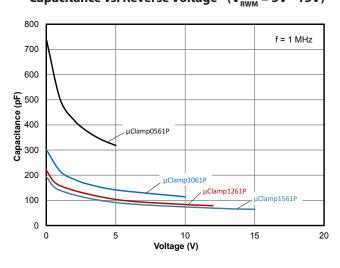
ESD Clamping (-8kV Contact per IEC 61000-4-2)



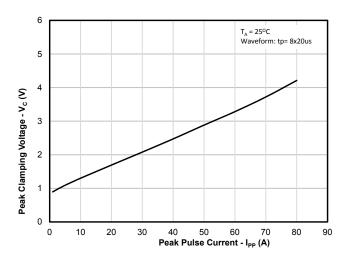
TLP Characteristic (Positive Pulse) - $(V_{RWM} = 5V - 15V)$



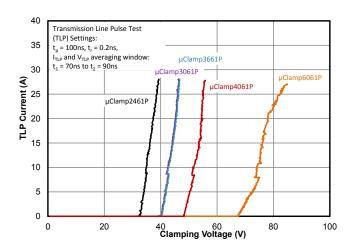
Capacitance vs. Reverse Voltage - $(V_{RWM} = 5V - 15V)$



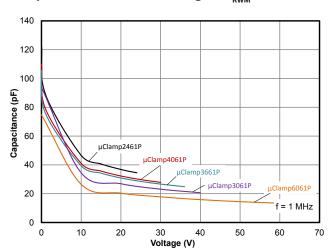
Forward Voltage vs. Peak Pulse Current (V_{RWM} = 5V - 60V)



TLP Characteristic (Positive Pulse) - $(V_{RWM} = 24V - 60V)$



Capacitance vs. Reverse Voltage - (V_{RWM} = 24V - 60V)



Application Information

Assembly Guidelines

The figure at the right details Semtech's recommended mounting pattern. Recommended assembly guidelines are shown in Table 1. Note that these are only recommendations and should serve only as a starting point for design since there are many factors that affect the assembly process. Exact manufacturing parameters will require some experimentation to get the desired solder application. Semtech's recommended mounting pattern is based on the following design guidelines:

Land Pattern

The recommended land pattern follows IPC standards and is designed for maximum solder coverage. Detailed dimensions are shown elsewhere in this document.

Solder Stencil

Stencil design is one of the key factors which will determine the volume of solder paste deposited onto the land pad. The area ratio of the stencil aperture will determine how well the stencil will print. The area ratio takes into account the aperture shape, aperture size, and stencil thickness. An area ratio of 0.70 – 0.75 is preferred for the subject package. The area ratio of a rectangular aperture is given as:

Area Ratio = (L * W) / (2 * (L + W) * T)

Where:

L = Aperture Length

W = Aperture Width

T = Stencil Thickness

Semtech recommends a stencil thickness of 0.125mm for this device. The stencil should be laser cut with electropolished finish. The stencil should have a positive taper of approximately 5 degrees. Electro polishing and tapering the walls results in reduced surface friction and better paste release. Since this device has uneven pad sizes, the recommended stencil opening is 10% smaller than the size of the large pad and 25um larger than the size of the small pad. This is done to control solder height and keep the part planar during reflow. Solder paste with Type 3 or smaller particles are recommended.

Recommended Mounting Pattern

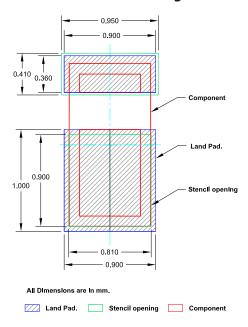
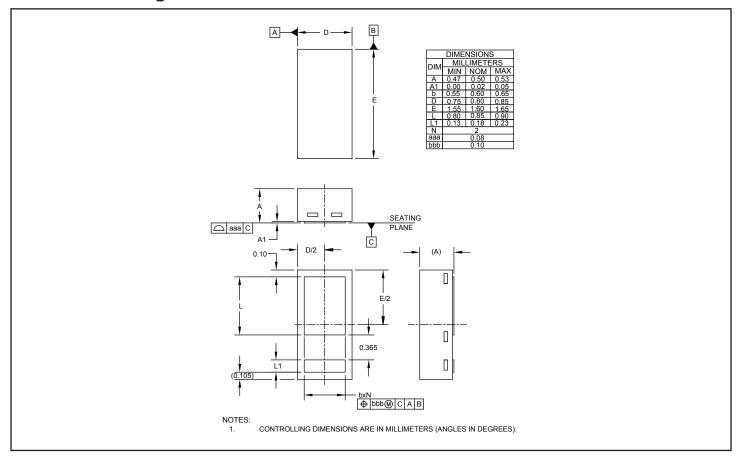
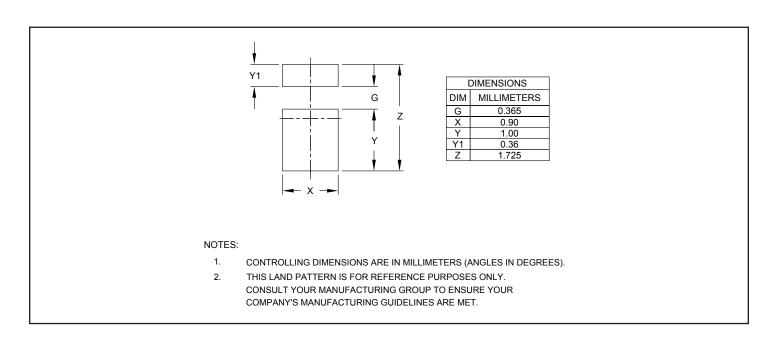


Table 1 - Recommended Assembly Guidelines							
Assembly Parameter	Recommendation						
Solder Stencil Design	Laser Cut, Electro-Polished						
Aperture Shape	Rectangular						
Solder Stencil Thickness	0.125mm (0.005")						
Solder Paste Type	Type 3 size sphere or smaller						
Solder Reflow Profile	Per JEDEC J-STD-020						
PCB Solder pad Design	Non-Solder Mask Defined						
PCB Pad Finish	OSP or NiAu						

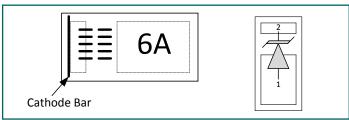
Outline Drawing - SLP1608P2



Land Pattern - SLP1608P2



Marking



Notes:

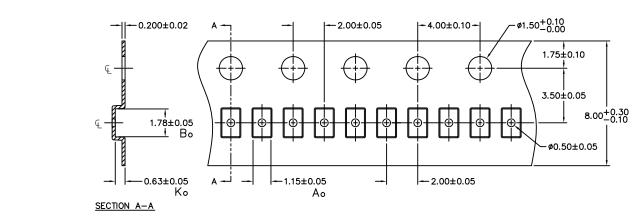
- 1) Dashes represent matrix date code
- 2) See ordering information for part specific marking codes

Ordering Information

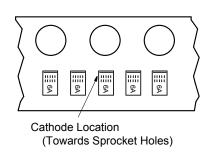
Part Number	Marking Code	Working Voltage	Qty per 7" Reel
μClamp0561P.TNT	6A	5V	10,000
μClamp1061P.TNT	6B	10V	10,000
μClamp1261P.TNT	6C	12V	10,000
μClamp1561P.TNT	6D	15V	10,000
μClamp2461P.TNT	6F	24V	10,000
μClamp3061P.TNT	6G	30V	10,000
μClamp3661P.TNT	6H	36V	10,000
μClamp4061P.TNT	6J	40V	10,000
μClamp6061P.TNT	6K	60V	10,000

Notes:

Tape and Reel Specification



NOTES: 1.) ALL DIMENSIONS IN MILLIMETERS UNLESS OTHERWISE SPECIFIED.



¹⁾ MicroClamp, uClamp and μ Clamp are trademarks of Semtech Corporaton



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ESD119B1W01005E6327XTSA1 ESD5V0L1B02VH6327XTSA1 ESD7451N2T5G 19180-510 CPDT-5V0USP-HF 3.0SMCJ33CA-F
3.0SMCJ36A-F HSPC16701B02TP D3V3Q1B2DLP3-7 D55V0M1B2WS-7 DESD5V0U1BL-7B DRTR5V0U4SL-7 SCM1293A-04SO
ESD200-B1-CSP0201 E6327 ESD203-B1-02EL E6327 SM12-7 SMF8.0A-TP SMLJ45CA-TP CEN955 W/DATA 82350120560
82356240030 VESD12A1A-HD1-GS08 CPDUR5V0R-HF CPDUR24V-HF CPDQC5V0U-HF CPDQC5V0USP-HF CPDQC5V0-HF
D1213A-01LP4-7B D1213A-02WL-7 ESDLIN1524BJ-HQ 5KP100A 5KP15A